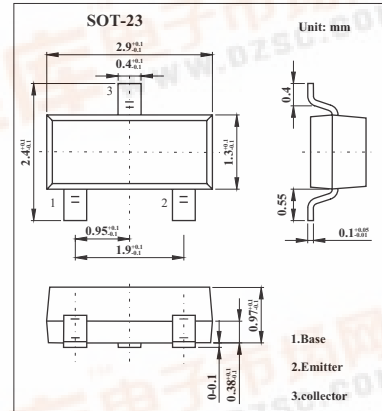


SMD Type Transistors

Epitaxial Planar PNP Silicon Transistor  
2SA1455K

Features

- High breakdown voltage:  $V_{CE0} = -120V$
- Low noise design:  $NF = 0.2dB$  (Typ.)



Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-120	V
Collector-emitter voltage	$V_{CE0}$	-120	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_c$	-50	mA
Collector power dissipation	$P_c$	200	mW
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CB0}$	$I_c = -50\mu A$	-120			V
Collector-emitter breakdown voltage	$BV_{CE0}$	$I_c = -1mA$	-120			V
Emitter-base breakdown voltage	$BV_{EB0}$	$I_E = -50\mu A$	-5			V
Collector cutoff current	$I_{CB0}$	$V_{CB} = -100V$			-0.5	$\mu A$
Emitter cutoff current	$I_{EB0}$	$V_{EB} = -4V$			-0.5	$\mu A$
DC current transfer ratio	$h_{FE}$	$V_{CE} = -6V, I_c = -2mA$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10mA, I_B = -1mA$			-0.5	V
Output capacitance	$f_T$	$V_{CE} = -12V, I_E = 2mA, f = 30MHz$		140		MHz
Transition frequency	$C_{ob}$	$V_{CB} = -12V, I_E = 0A, f = 1MHz$		3.2		pF

hFE Classification

Marking	G		
	R	S	E
hFE	180~390	270~560	390~820

